



# PMV30UN2

20 V, N-channel Trench MOSFET

24 April 2014

Product data sheet

## 1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

## 2. Features and benefits

- Trench MOSFET technology
- Low threshold voltage
- Very fast switching
- Enhanced power dissipation capability of 1000 mW

## 3. Applications

- LED driver
- Power management
- Low-side load switch
- Switching circuits

## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{DS}$	drain-source voltage	$T_j = 25\text{ °C}$	-	-	20	V
$V_{GS}$	gate-source voltage		-12	-	12	V
$I_D$	drain current	$V_{GS} = 4.5\text{ V}; T_{amb} = 25\text{ °C}; t \leq 5\text{ s}$	[1]	-	5.4	A
<b>Static characteristics</b>						
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 4.5\text{ V}; I_D = 4.2\text{ A}; T_j = 25\text{ °C}$	-	24	32	mΩ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

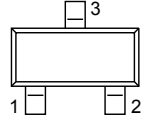
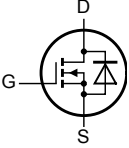


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## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	 <p>TO-236AB (SOT23)</p>	 <p>017aaa253</p>
2	S	source		
3	D	drain		

## 6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PMV30UN2	TO-236AB	plastic surface-mounted package; 3 leads	SOT23

## 7. Marking

Table 4. Marking codes

Type number	Marking code
PMV30UN2	%K6

[1] % = placeholder for manufacturing site code

## 8. Limiting values

**Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{DS}$	drain-source voltage	$T_j = 25\text{ °C}$		-	20	V
$V_{GS}$	gate-source voltage			-12	12	V
$I_D$	drain current	$V_{GS} = 4.5\text{ V}; T_{amb} = 25\text{ °C}; t \leq 5\text{ s}$	[1]	-	5.4	A
		$V_{GS} = 4.5\text{ V}; T_{amb} = 25\text{ °C}$	[1]	-	4.2	A
		$V_{GS} = 4.5\text{ V}; T_{amb} = 100\text{ °C}$	[1]	-	2.7	A
$I_{DM}$	peak drain current	$T_{amb} = 25\text{ °C}; \text{single pulse}; t_p \leq 10\text{ }\mu\text{s}$		-	18	A
$P_{tot}$	total power dissipation	$T_{amb} = 25\text{ °C}$	[2]	-	490	mW
			[1]	-	1000	mW
		$T_{sp} = 25\text{ °C}$		-	5000	mW
$T_j$	junction temperature			-55	150	°C
$T_{amb}$	ambient temperature			-55	150	°C
$T_{stg}$	storage temperature			-65	150	°C
<b>Source-drain diode</b>						
$I_S$	source current	$T_{amb} = 25\text{ °C}$	[1]	-	0.9	A

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain  $6\text{ cm}^2$ .
- [2] Device mounted on an FR4 Printed Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

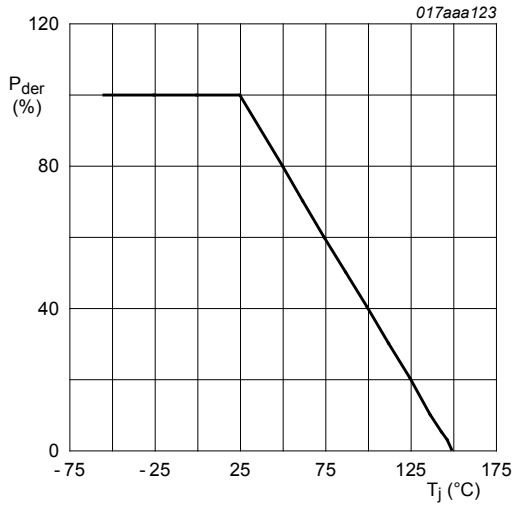


Fig. 1. MOSFET transistor: Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

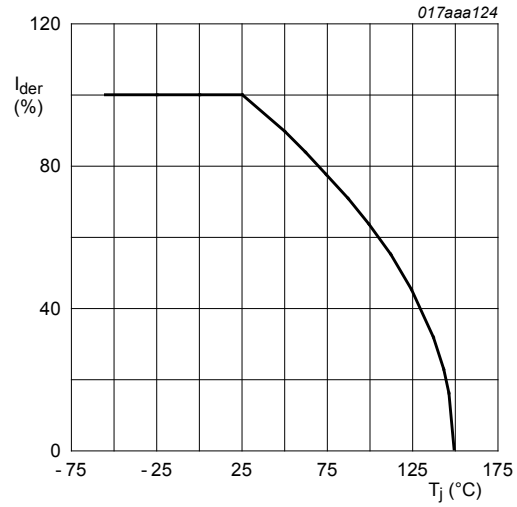
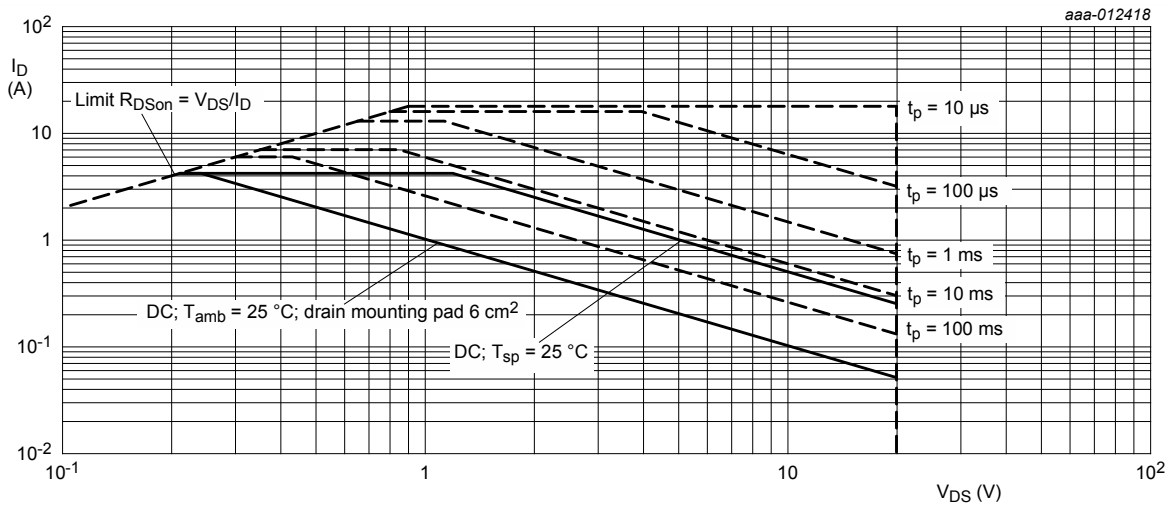


Fig. 2. MOSFET transistor: Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$



I<sub>DM</sub> = single pulse

Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

## 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	[1]	-	217	255	K/W
			[2]	-	105	124	K/W
		t ≤ 5 s	[2]	-	73	86	K/W

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point		-	20	25	K/W

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

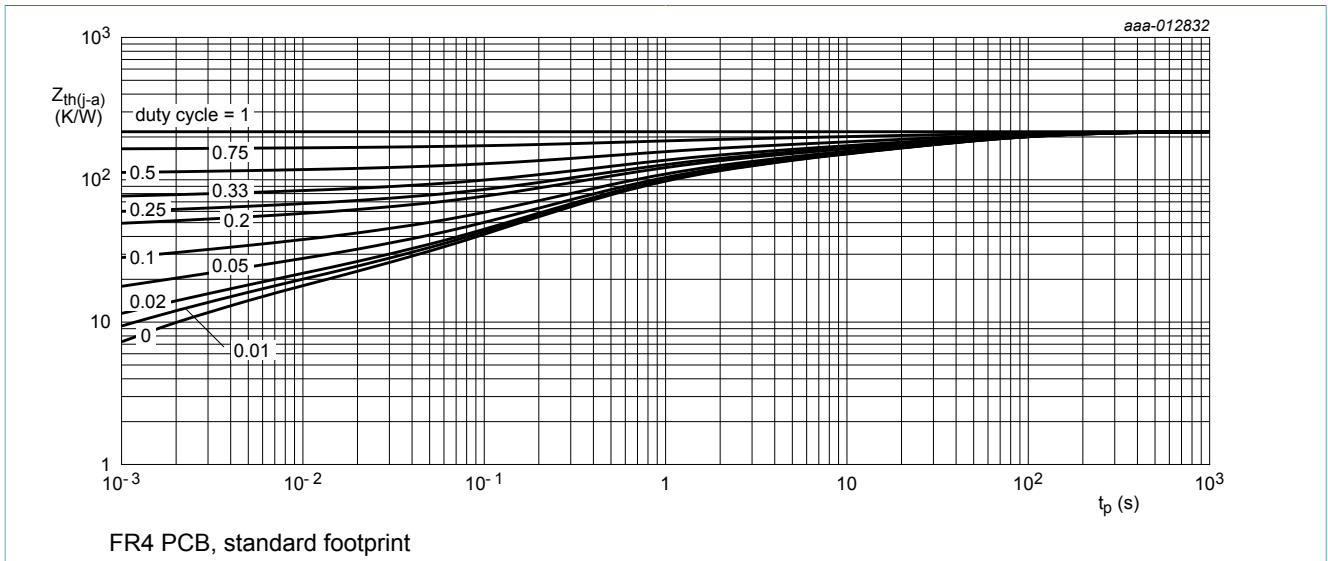


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

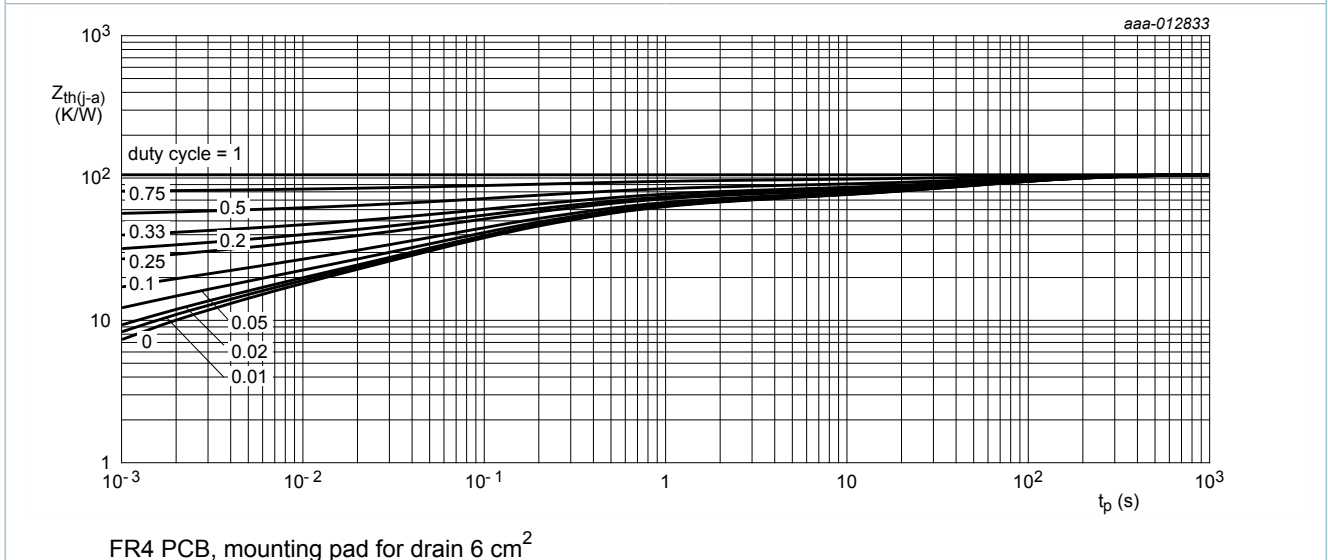
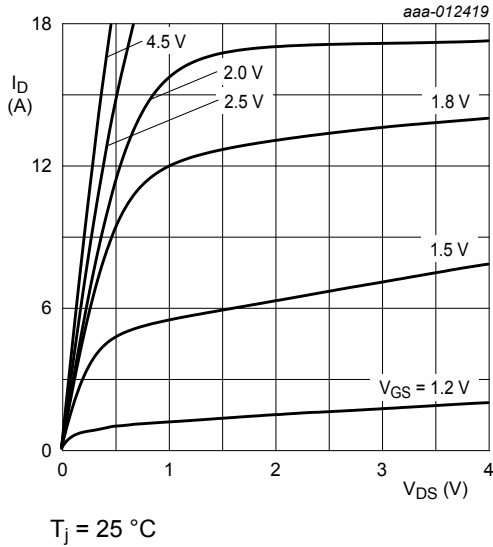


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

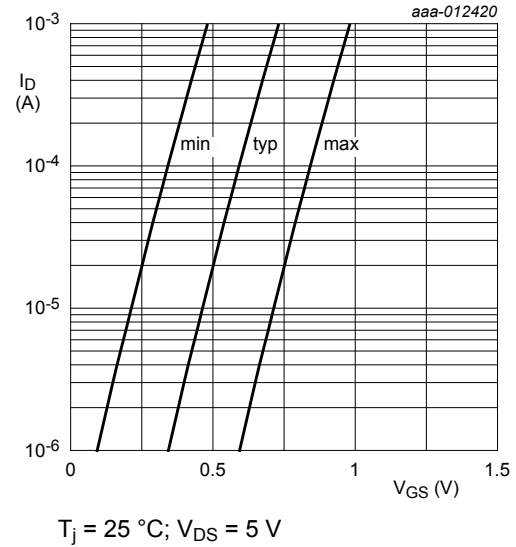
## 10. Characteristics

Table 7. Characteristics

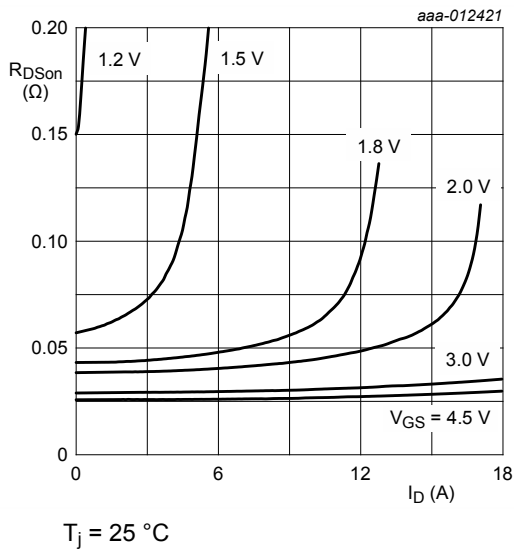
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	20	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ C$	0.4	0.65	0.9	V
$I_{DSS}$	drain leakage current	$V_{DS} = 20 V; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	-	-	1	$\mu A$
$I_{GSS}$	gate leakage current	$V_{GS} = 12 V; V_{DS} = 0 V; T_j = 25 \text{ }^\circ C$	-	-	100	nA
		$V_{GS} = -12 V; V_{DS} = 0 V; T_j = 25 \text{ }^\circ C$	-	-	-100	nA
$R_{DSon}$	drain-source on-state resistance	$V_{GS} = 4.5 V; I_D = 4.2 A; T_j = 25 \text{ }^\circ C$	-	24	32	m $\Omega$
		$V_{GS} = 4.5 V; I_D = 4.2 A; T_j = 150 \text{ }^\circ C$	-	37	50	m $\Omega$
		$V_{GS} = 2.5 V; I_D = 3.7 A; T_j = 25 \text{ }^\circ C$	-	30	43	m $\Omega$
		$V_{GS} = 1.8 V; I_D = 1.0 A; T_j = 25 \text{ }^\circ C$	-	40	59	m $\Omega$
		$V_{GS} = 1.5 V; I_D = 0.1 A; T_j = 25 \text{ }^\circ C$	-	56	100	m $\Omega$
		$V_{GS} = 1.2 V; I_D = 10 \text{ mA}; T_j = 25 \text{ }^\circ C$	-	160	-	m $\Omega$
$g_{fs}$	forward transconductance	$V_{DS} = 10 V; I_D = 2 A; T_j = 25 \text{ }^\circ C$	-	15.8	-	S
$R_G$	gate resistance	$f = 1 \text{ MHz}; T_j = 25 \text{ }^\circ C$	-	7.6	-	$\Omega$
<b>Dynamic characteristics</b>						
$Q_{G(tot)}$	total gate charge	$V_{DS} = 10 V; I_D = 4.2 A; V_{GS} = 4.5 V; T_j = 25 \text{ }^\circ C$	-	6.2	11	nC
$Q_{GS}$	gate-source charge		-	0.8	-	nC
$Q_{GD}$	gate-drain charge		-	1.4	-	nC
$C_{iss}$	input capacitance	$V_{DS} = 10 V; f = 1 \text{ MHz}; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	-	655	-	pF
$C_{oss}$	output capacitance		-	70	-	pF
$C_{rss}$	reverse transfer capacitance		-	62	-	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 10 V; I_D = 4.2 A; V_{GS} = 4.5 V; R_{G(ext)} = 6 \text{ } \Omega; T_j = 25 \text{ }^\circ C$	-	7	-	ns
$t_r$	rise time		-	26	-	ns
$t_{d(off)}$	turn-off delay time		-	35	-	ns
$t_f$	fall time		-	10	-	ns
<b>Source-drain diode</b>						
$V_{SD}$	source-drain voltage	$I_S = 0.9 A; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	-	0.7	1.2	V



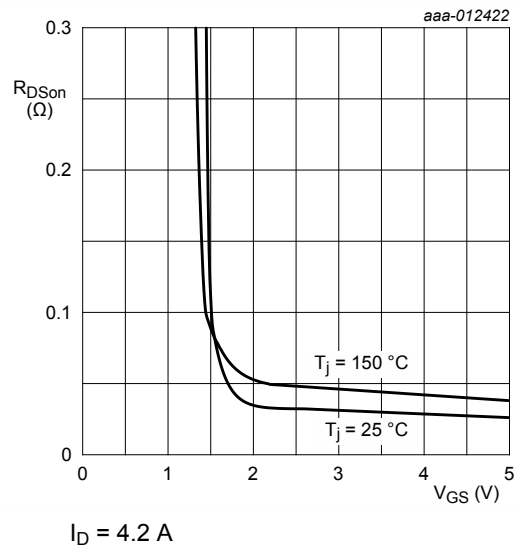
**Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values**



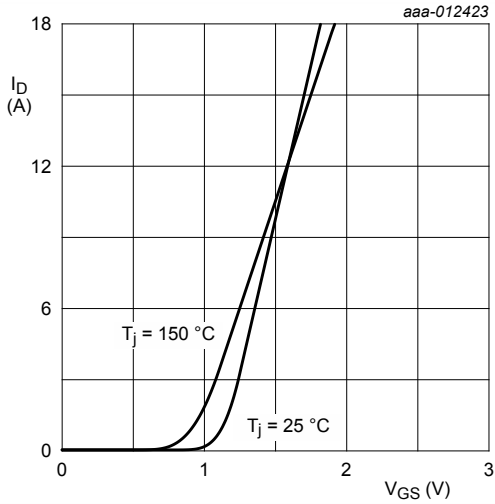
**Fig. 7. Sub-threshold drain current as a function of gate-source voltage**



**Fig. 8. Drain-source on-state resistance as a function of drain current; typical values**



**Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values**



$$V_{DS} > I_D \times R_{DSon}$$

Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

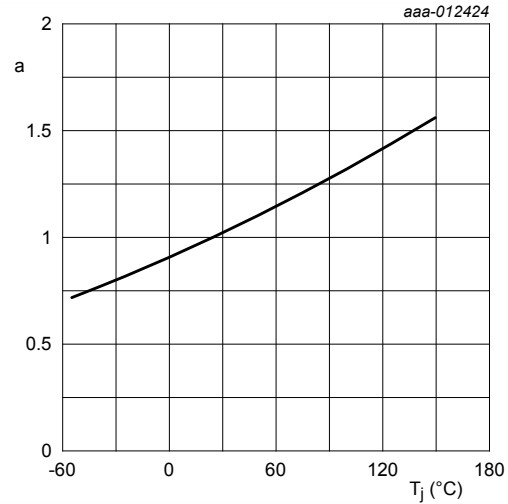
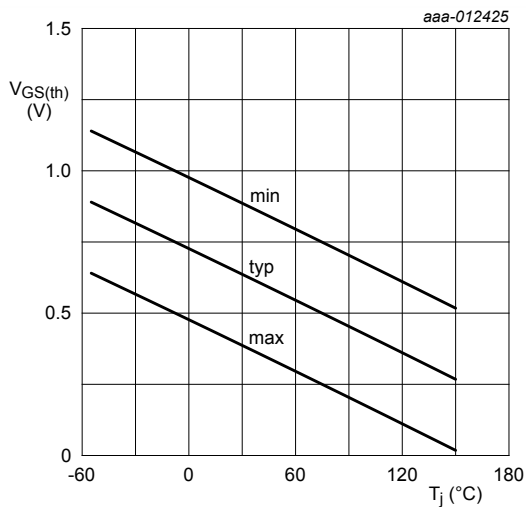


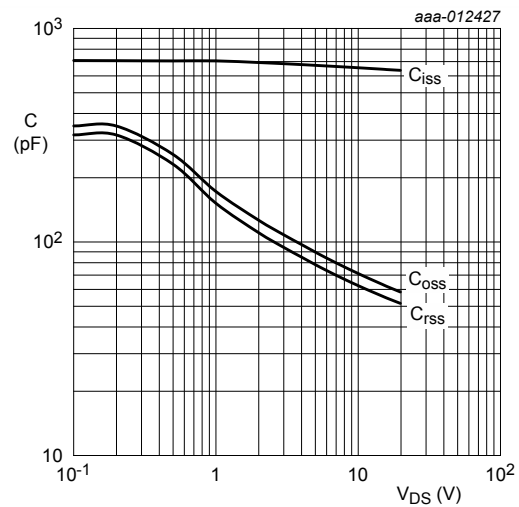
Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^\circ C)}}$$



$$I_D = 250 \mu A; V_{DS} = V_{GS}$$

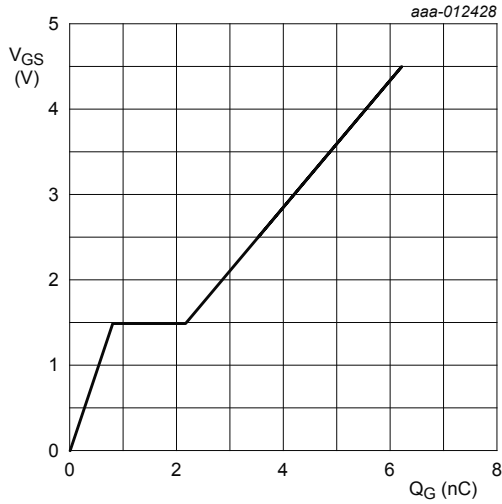
Fig. 12. Gate-source threshold voltage as a function of junction temperature



$$f = 1 \text{ MHz}; V_{GS} = 0 \text{ V}$$

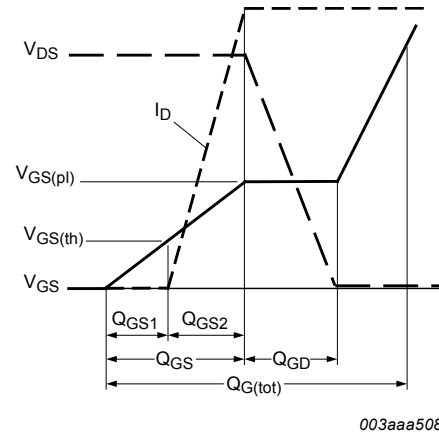
Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values





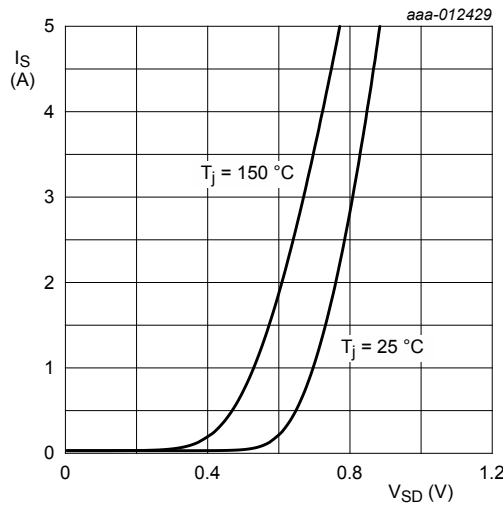
$I_D = 4.2 \text{ A}$ ;  $V_{DS} = 10 \text{ V}$ ;  $T_{amb} = 25 \text{ }^\circ\text{C}$

Fig. 14. Gate-source voltage as a function of gate charge; typical values



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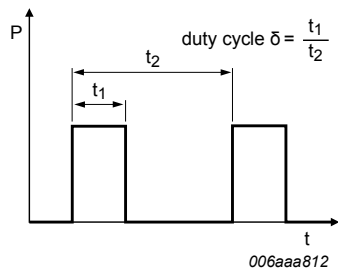
Fig. 15. MOSFET transistor: Gate charge waveform definitions



$V_{GS} = 0 \text{ V}$

Fig. 16. Source current as a function of source-drain voltage; typical values

## 11. Test information



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Fig. 17. Duty cycle definition

## 12. Package outline

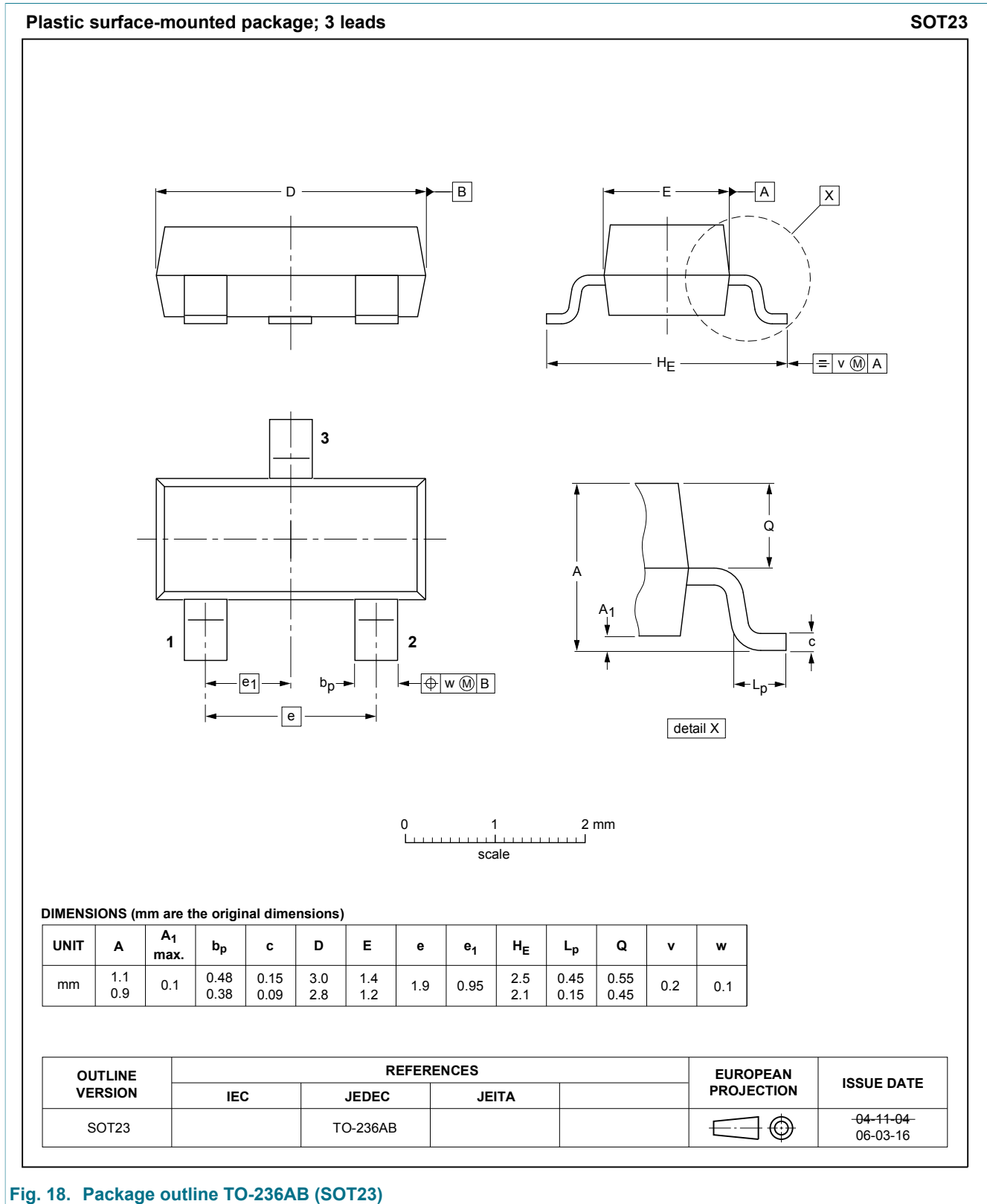


Fig. 18. Package outline TO-236AB (SOT23)

### 13. Soldering

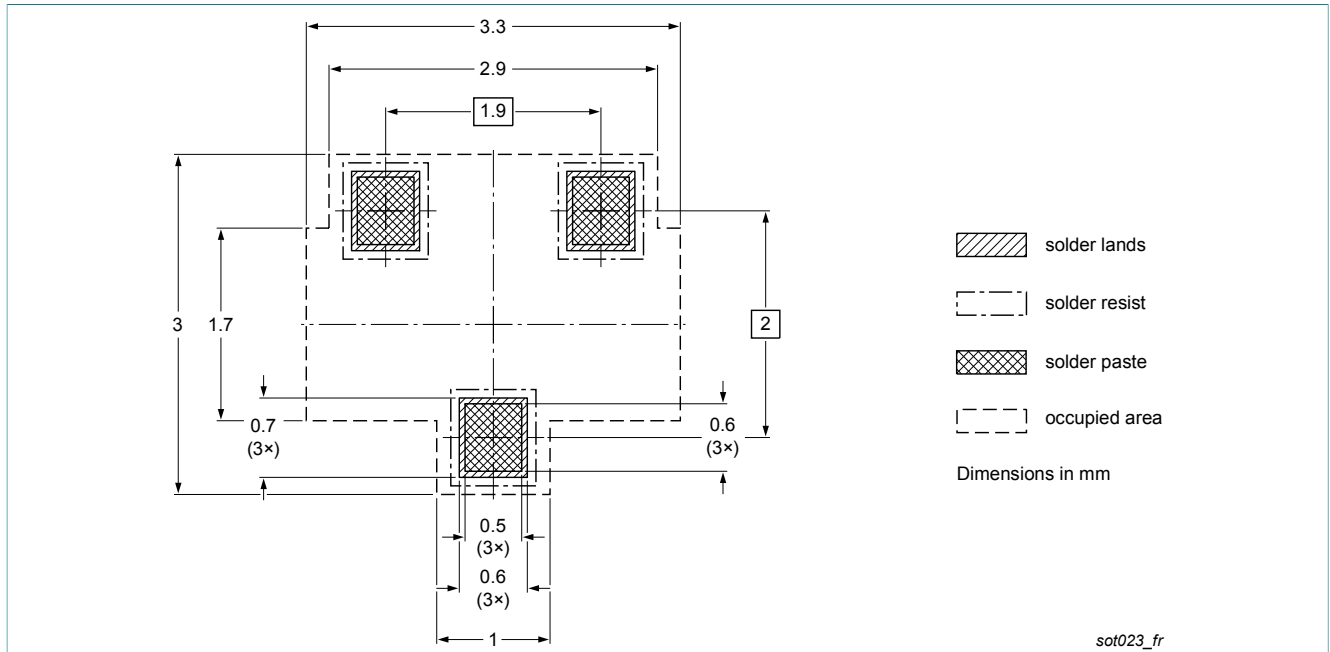


Fig. 19. Reflow soldering footprint for TO-236AB (SOT23)

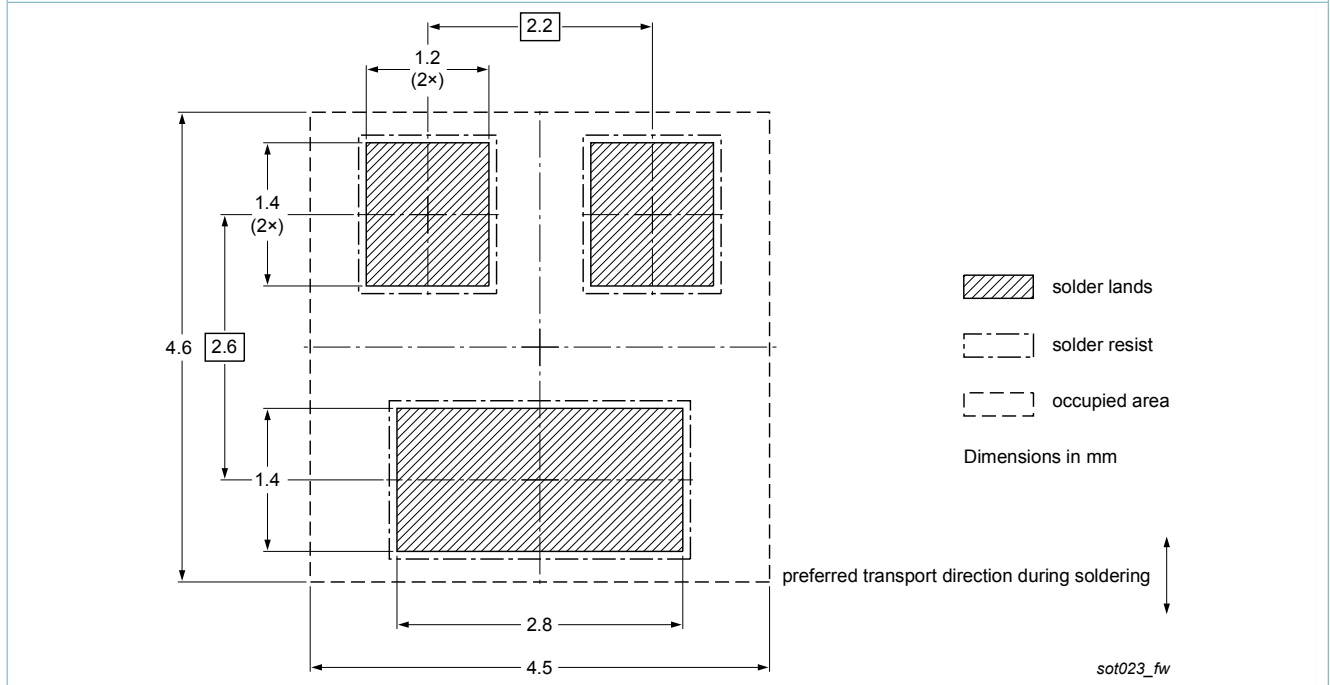


Fig. 20. Wave soldering footprint for TO-236AB (SOT23)

## 14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMV30UN2 v.1	20140424	Product data sheet	-	-

## 15. Legal information

### 15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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Date of release: 24 April 2014